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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: To Be Assigned Examiner: To Be Assigned

In Re PATENT APPLICATION Of:

Applicants : Toyokazu Sakata

Serial No. : To Be Assigned

Filed: November 26, 2003

For : ETCHING METHOD AND

SEMICONDUCTOR DEVICE FABRICATING METHOD

Attorney Ref.: TAI 145

November 26, 2003

INFORMATION

DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

This is an information disclosure statement submitted in compliance with the timing requirements of 37 C.F.R. §1.97(b)(1).

Attached are copies of two Japanese patent publications and two English -language publications. Any relevance of the Japanese patents can be gleaned from the attached English-language Abstracts. The one of the Japanese publications and both English-language publications are listed on the attached Form PTO-1449 and discussed on pages 2 and 3 of the application. Also listed on the form PTO-1449 for consideration is one U.S. Patent. As the present application was filed after June 30, 2003, a copy of the U.S. Patent is not submitted with the Information Disclosure Statement, pursuant to the Notice of U.S. Patent & Trademark Office posted on the USPTO website on July 11, 2003.

Since this Information Disclosure Statement is being filed with the application, no certification or fee is required, and the requirements of 37 C.F.R. §§1.97 and 1.98 are deemed to be fully met as to the documents submitted. Consideration of the submitted and listed documents is respectfully requested.

Respectfully submitted.

November 26, 2003

Date

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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT				Atty Docket	Applica	Application No. To Be Assigned		
				TAI 145	To Be			
				Applicant	Applicant			
				Toyokazu Sakata				
				Filing Date	Group	Group Unit		
				November 26, 2003	To Be	e Assign	ed	
			U.S.	PATENT DOCUMENTS				
Examiner Initial		Document Number	Date	Name	Class	Sub- Class	Filing Date	
	AA	6,355.572	03/12/02	Ikegami				
ļ	AB							
	AC							
	AD							
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		1	FOREIC	GN PATENT DOCUMENTS	- - 		T	
		Document Number	Date	Country	Class	Sub- Class	Trans- lation	
	AK	7-94483	04/07/95	Japan	·		Abstract	
	AL	2001-77086	03/23/01	Japan			Abstract	
_	AM							
	AN	<u> </u>						
				Author, Title, Date, Pertinent Pages, et				
	AO	"Dry Etching of Organic Low Dielectric Constant Film without Etch Stop Layer" M.Mizumura et al. JJAP, Vol. 41, pp. 425-427						
	AP	"Highly Selective Etching of Organic SOG to SiN for Cu Damascene Interconnects Using New Gas Chemistry of C ₄ F ₈ /N ₂ /Ar" S. Uno et al. Proc. Of Dry Process Symp., pp. 215-220(1999)						
	AQ							
Examiner	<u>.</u>			Date Consider	red			
				er or not citation is in conformance with				